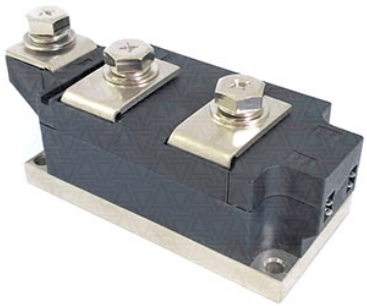
АС ЭНЕРГИЯ

Модуль диодный
МДД-500-26



Средний прямой ток				I_{FAV}		500 А				
Повторяющееся импульсное обратное напряжение				U_{RRM}		800 - 2600 В				
U_{RRM}, В	800	1000	1200	1400	1600	1800	2000	2200	2400	2600
Класс по напряжению	8	10	12	14	16	18	20	22	24	26
T_j, °C	-60 ÷ 150									

SYMBOL	CHARACTERISTIC	TEST CONDITIONS	T_j(°C)	VALUE			UNIT
				Min	Type	Max	
$I_{F(AV)}$	Mean forward current	180° half sine wave 50Hz Single side cooled, T_C=100°C	150			500	A
$I_{F\ (RMS)}$	RMS forward current		150			785	A
I_{RRM}	Repetitive peak current	at V_{RRM}	150			40	mA
I_{FSM}	Surge forward current	10ms half sine wave V_R=0.6V_{RRM}	150			16.0	KA
I^2t	I^2T for fusing coordination					1280	A^2s*10^3
V_{FO}	Threshold voltage		150			0.75	V
r_F	Forward slop resistance					0.30	mΩ
V_{FM}	Peak forward voltage	I_{FM}=1800A	25			1.45	V
$R_{th(j-c)}$	Thermal resistance Junction to case	At 180°sine, Single side cooled per chip				0.090	°C /W
$R_{th(c-h)}$	Thermal resistance case to heatsink	At 180° sine, Single side cooled per chip				0.024	°C /W
V_{iso}	Isolation voltage	50Hz,R.M.S,t=1min,I_{iso}:1mA(max)		3000			V
F_m	Terminal connection torque(M10)				12.0		N·m
	Mounting torque(M6)				6.0		N·m
T_{stg}	Stored temperature			-40		125	°C
W_t	Weight				1430		g
Outline	MTD5						

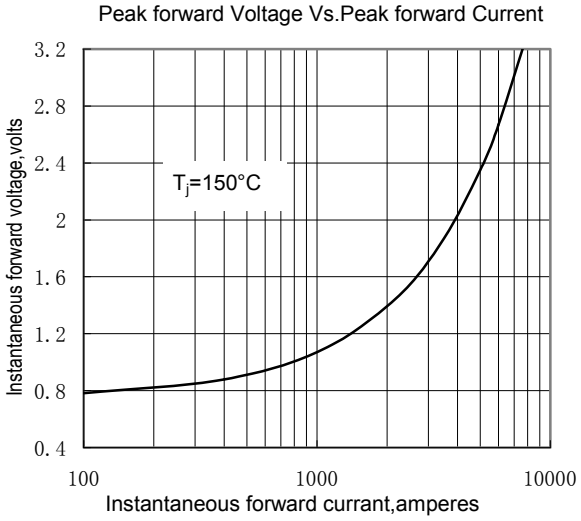


Fig.1

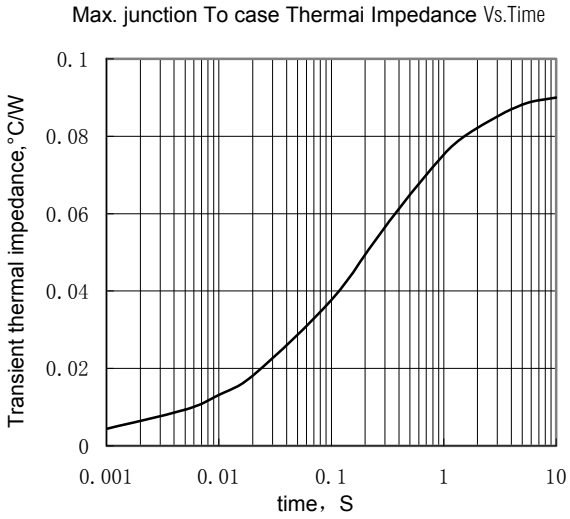


Fig.2

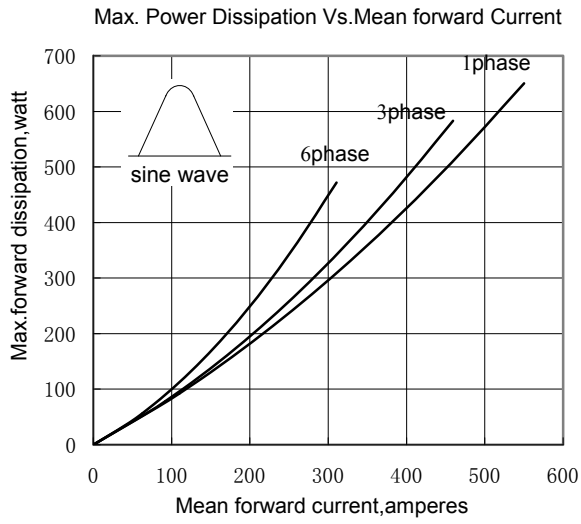


Fig.3

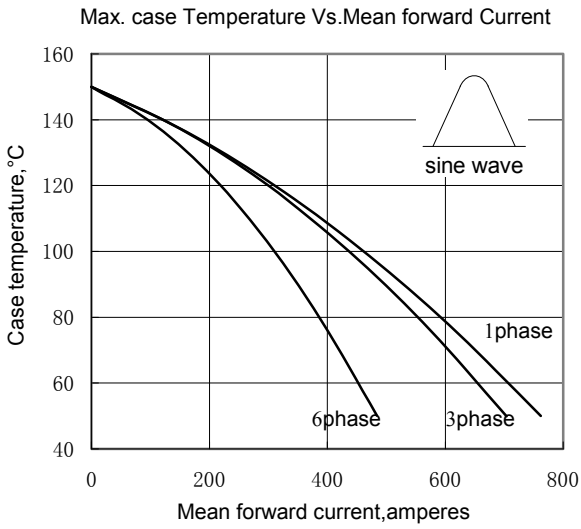


Fig.4

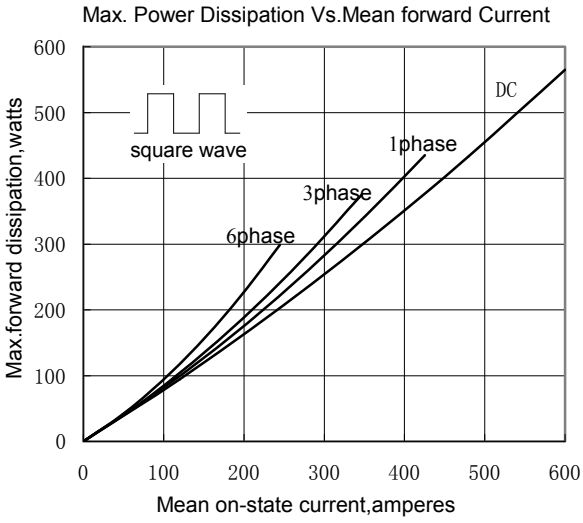


Fig.5

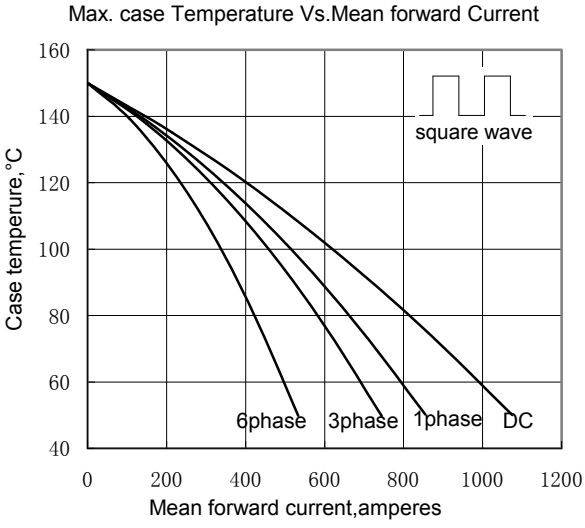


Fig.6

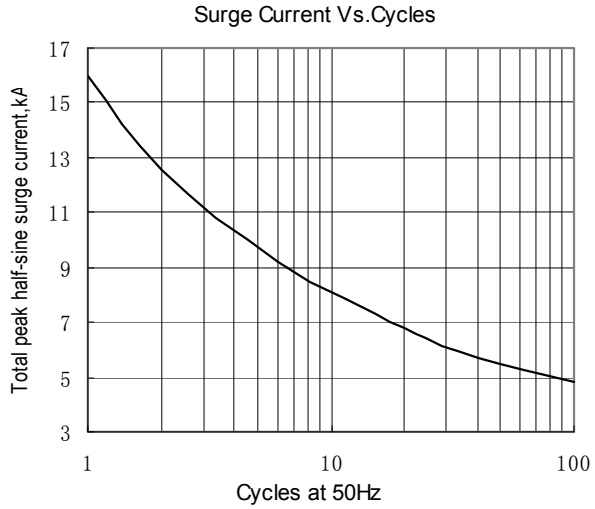


Fig.7

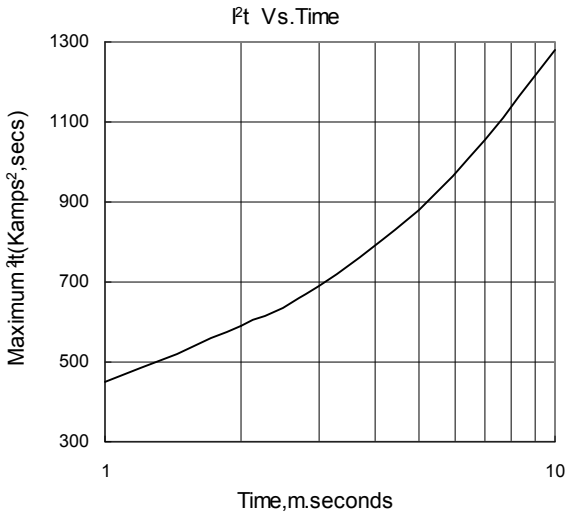
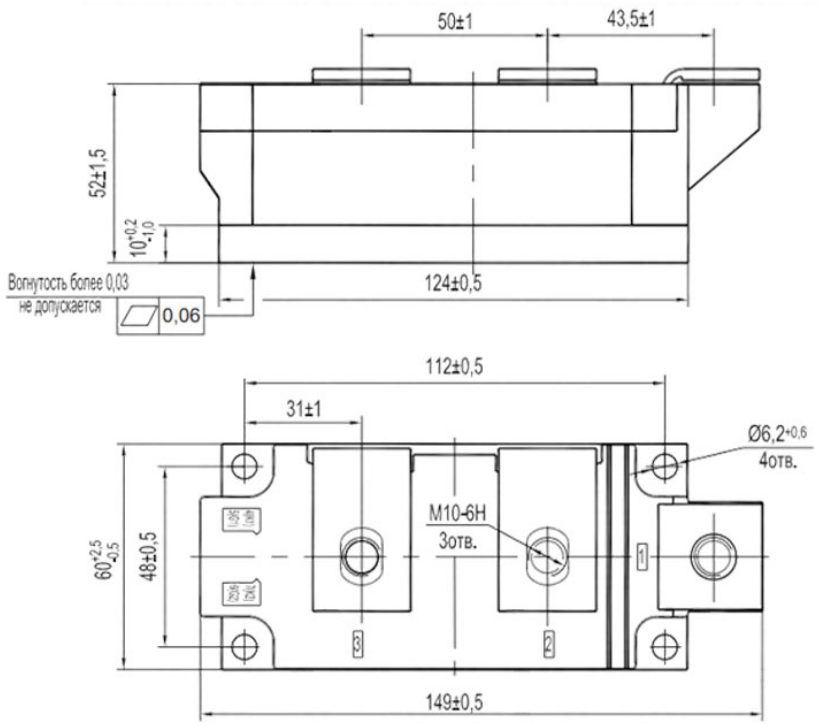


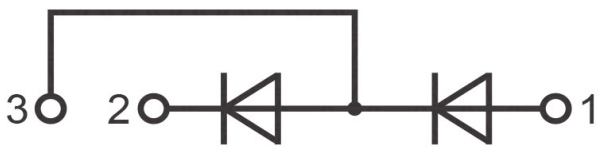
Fig.8

ГАБАРИТНЫЕ РАЗМЕРЫ

Тип корпуса: MDT5



Все размеры в миллиметрах



3 – Анод/Катод, 2 – Катод, 1 – Анод